

ILMS5360

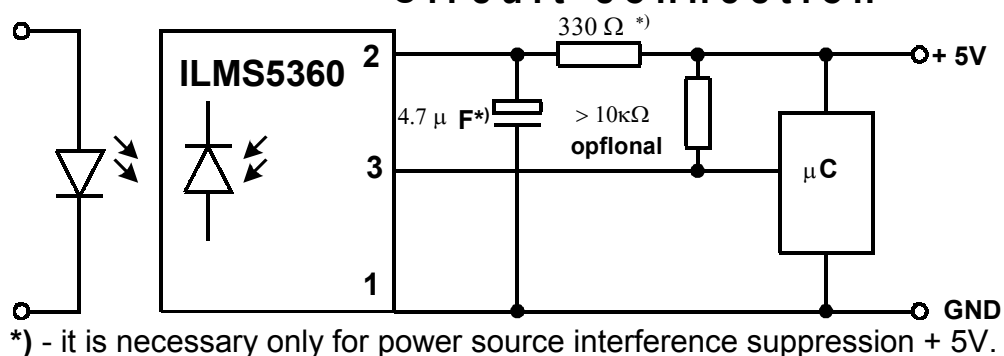
Absolute Maximum Ratings Tamb=25°C

Parameter	Test conditions	Symbol	Value	Unit
Supply voltage		Vs	0.3 ÷ 6.0	V
Power current		Is	1.0	mA
Junction temperature		T _j	100	°C
Storage temperature		T _{stg}	-25 ÷ +85	°C
Operating temperature		T _{amb}	-25 ÷ +85	°C
Power consumption	(T _{amb} = 85 °C)	P _{tot}	50	mW

Basic characteristics Tamb=25°C

Parameter	Test conditions	Symbol	MIN	TYP	MAX	Unit.
Current consumption (Pin 2)	Vs = 5 V, Ev = 0	I _{SD}	0.4	0.5	0.8	mA
Current consumption (Pin 2)	Vs = 5 V, Ev = 40 klx, sunlight	I _{SH}	-	1.0	-	mA
Output voltage of low level (Pin 3)	I _{OSL} = 0.5 mA, U _s =5.0 V E _e = 0.7 mW/M ² , f=f ₀ , t _p /N=0,4 Test signal	V _{OSL}	-	-	250	mV
Minimum density of IR-radiating power	t _{PO} =t _{PI} ±160 MKC Test signal	E _{emin}		0.4	0.6	mW/m ²
Maximum radiation IR-radiating power	Test signal	E _{emax}	20	-	-	W/m ²

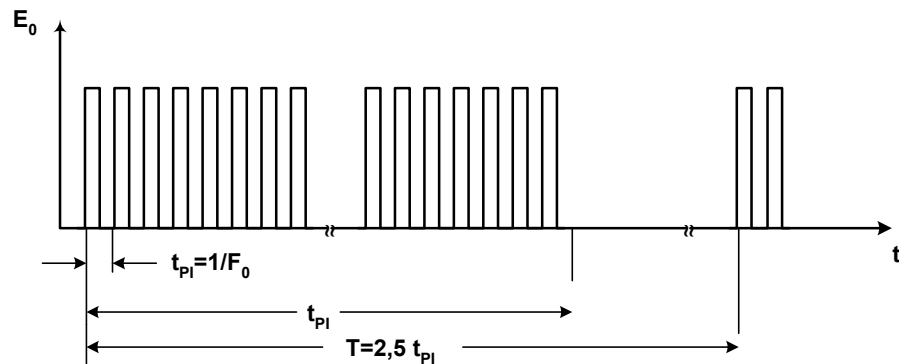
Circuit connection



Korzhenevskogo 12, Minsk, 220064, Republic of Belarus
 Fax: +375 (17) 278 28 22,
 Phone: +375 (17) 278 07 11, 277 24 70, 277 24 61,
 277 69 16
 E-mail: belms@belms.belpak.minsk.by
 URL: www.bms.by

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Input test signal



Output signal

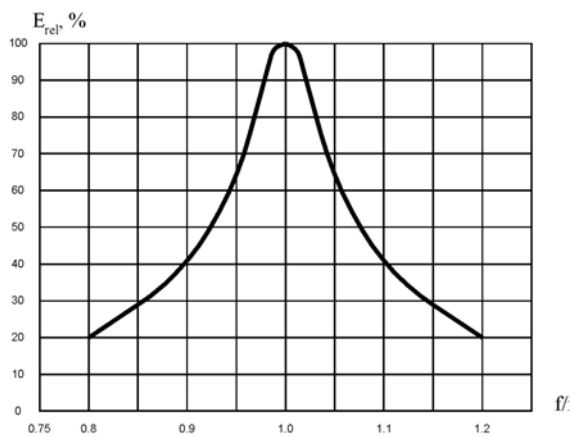
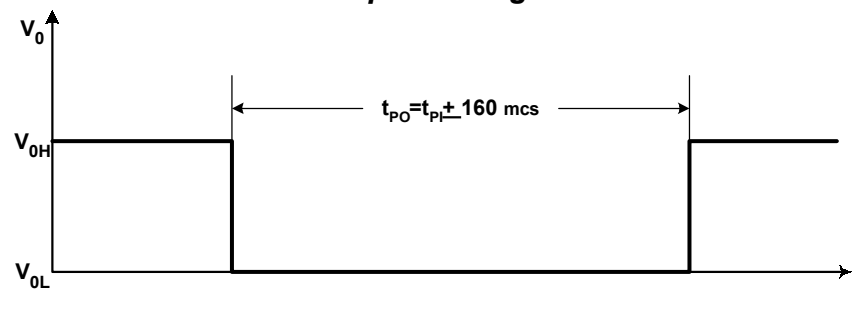


Figure 1 – Dependence of sensitivity as function of normalized frequency, $T_{amb} = 25^{\circ}C$ (amplitude-frequency response).

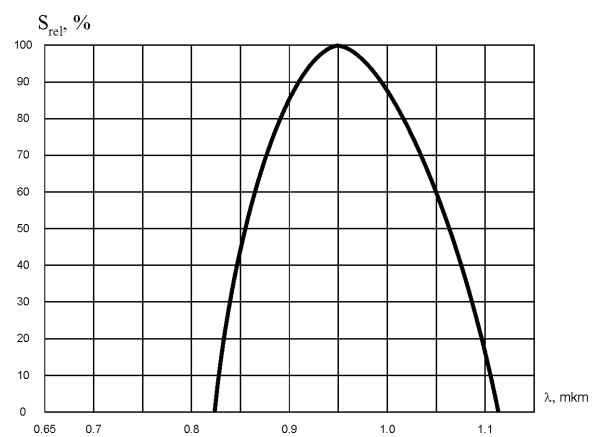


Figure 2 – Dependence of sensitivity on IR-radiation wave length by $T_{amb} = 25^{\circ}C$ (spectral response).



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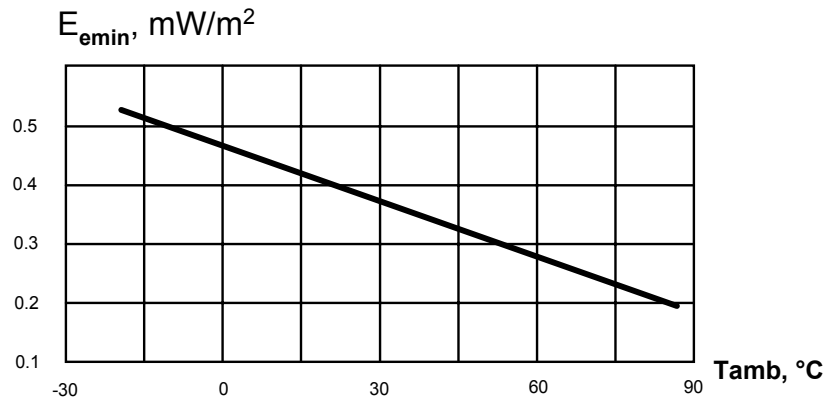


Figure 3 – Dependence of IR radiation minimum power density parameter on environment temperature (microcircuit sensibility) by $U_s = 5B$.

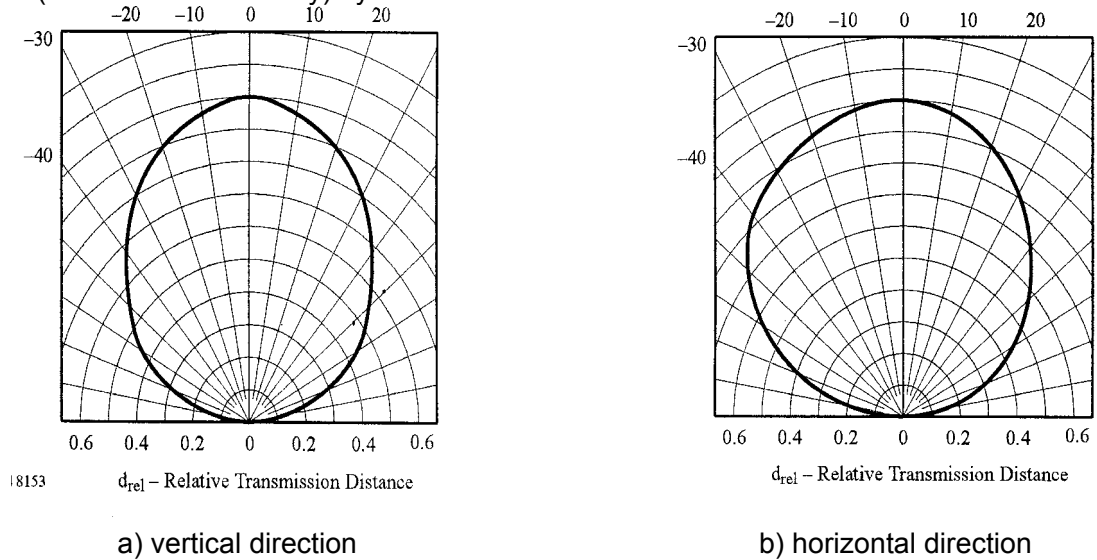


Figure 4 – Dependence of relative sensitivity on infra-red source angle turn.

